: 5 .> / / x 4 6 4 ! - } â ’ož Silicon NPN transistor in a TO-252 Plastic Package.

Ã a ? d / Absolute Maximum Ratings(Ta=25 ;)

@ ƒ Parameter	… Z Symbol	ƒ › Rating	% y Unit
Collector to Base Voltage	V_{CBO}	100	V
Collector to Emitter Voltage	V_{CEO}	100	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	2.0	A
Collector Current – Continuous(Pulse)	$I_{C(Pulse)}$	4.0	A
Base Current - Continuous	I_B	50	mA
Collector Power Dissipation	P_C	1.75	W
Collector Power Dissipation	$P_C(T_C=25$)	20	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

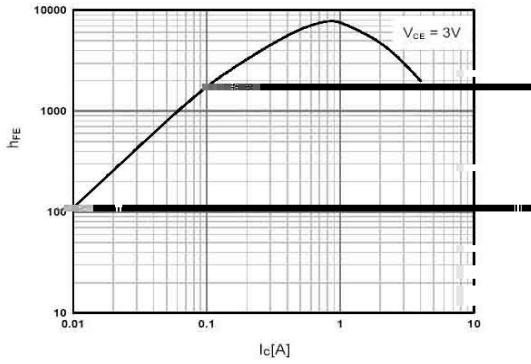
Pulse Test:PW ”300 s,Duty Cycle ”2%

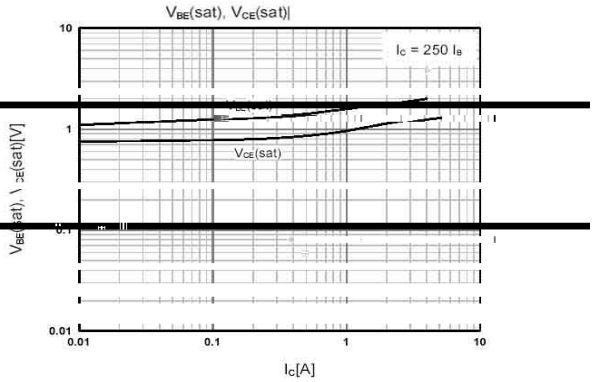
Ô4ì × ? d / Electrical Characteristics(Ta=25 ;)

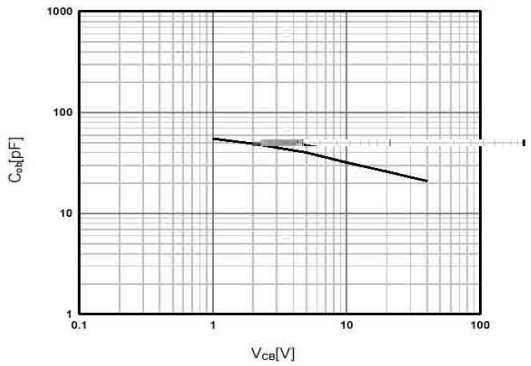
@ ƒ Parameter	… Z Symbol	y ¡ Ú ^ Test Conditions	Â 4 › Min	Á º › Typ	Â Ý › Max	% y Unit
Collector to Emitter Breakdown Voltage*	V_{CEO*}	I_C=10mA I_B=0	100			V
Collector Cut-Off Current	I_{CEO}	V_{CE}=50V I_B=0			0.02	mA
Collector Cut-Off Current	I_{CBO}	V_{CB}=100V I_E=0			0.02	mA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=5.0V I_C=0			2.0	mA
DC Current Gain	$h_{FE(1)*}$	V_{CE}=3.0V I_C=2.0A	1000		12K	
	$h_{FE(2)*}$	V_{CE}=3.0V I_C=0.5A	500			
	$h_{FE(3)*}$	V_{CE}=3.0V I_C=4.0A	200			
Collector-Emitter Saturation Voltage	$V_{CE(sat)1*}$	I_C=2.0A I_B=8.0mA			2.0	V
	$V_{CE(sat)2*}$	I_C=4.0A I_B=40mA			3.0	V
Base-Emitter Saturation Voltage*	$V_{BE(sat)*}$	I_C=4.0A I_B=40mA			4.0	V
Base-Emitter-On Voltage*	$V_{BE(on)*}$	V_{CE}=3.0V I_C=2.0A			2.8	V
Current Gain Bandwidth Product	f_T	V_{CE}=10V I_C=0.75A	25			MHz
Output Capacitance	C_{ob}	V_{CB}=10V I_E=0 f=0.1MHz			100	pF

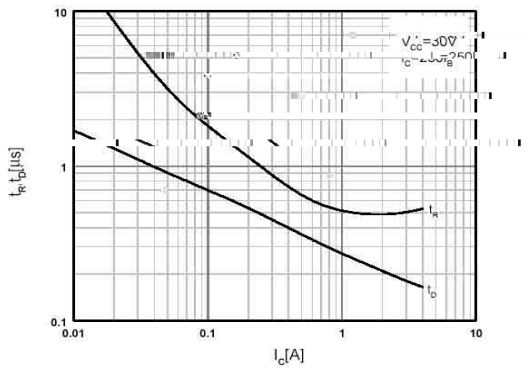
*Pulse Test:Pulse Width ”380us,Duty Cycle ”2%. Ï y ¡ y ! ‡ [Y) q A ‡ ož

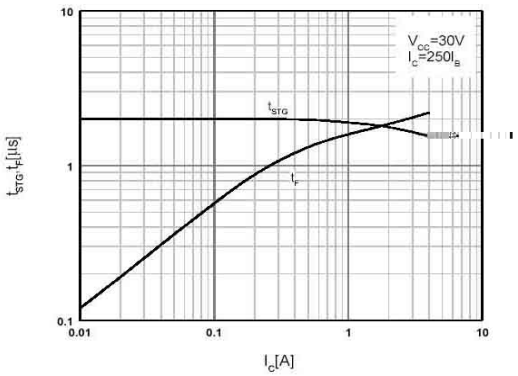
Ô ? d • Ž ¢ / Electrical Characteristic Curve

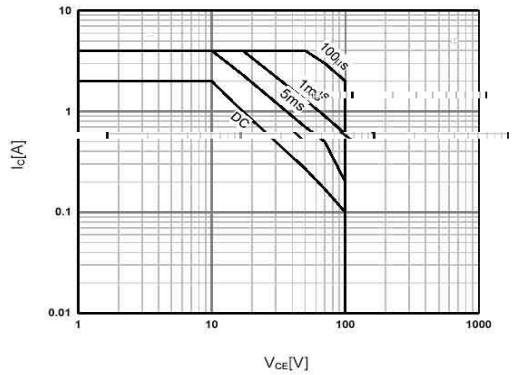


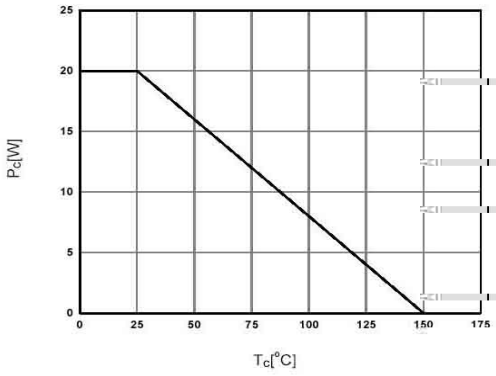












Ø ¤ =) ¢ / Package Dimensions

